Analog Power AM30N10-78D

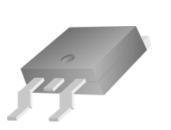
N-Channel 100-V (D-S) MOSFET

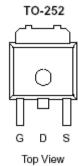
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY			
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$	
100	$78 @ V_{GS} = 10V$	21	
	98 @ V _{GS} = 4.5V	19	

DDODUCT CUMMADY

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	v
Continuous Drain Current ^a	T _C =25°C	I_{D}	21	_
Pulsed Drain Current ^b		I_{DM}	36	A
Continuous Source Current (Diode Conduction) ^a		I_S	30	A
Power Dissipation ^a	T _C =25°C	P_{D}	50	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{ heta JA}$	50	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3.0	°C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Crumbal	T-4 C 14	Limits			T Inni4
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static					•	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	$I_{ m DSS}$ -	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Drain Current	DSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	34			A
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$			78	mΩ
Drain-Source Oil-Resistance		$V_{GS} = 4.5 \text{ V}, I_{D} = 1 \text{ A}$			98	
Forward Tranconductance ^A	${f g}_{ m fs}$	$V_{DS} = 40 \text{ V}, I_{D} = 1 \text{ A}$		4.4		S
Diode Forward Voltage	V_{SD}	$I_{S} = 1 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V
Dynamic ^b						
Total Gate Charge	Q_{g}	V - 25 V V - 10 V		9		
Gate-Source Charge	Q_{gs}	$V_{DS} = 25 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} = 1 \text{ A}$		3		nC
Gate-Drain Charge	Q_{gd}			3		
Turn-On Delay Time	$t_{d(on)}$			4		
Rise Time	$t_{\rm r}$	$V_{DD} = 100 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$		2		nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		20] 113
Fall-Time	$t_{\rm f}$			5		

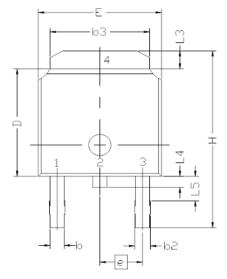
Notes

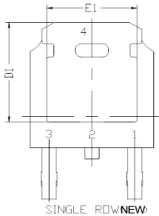
a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

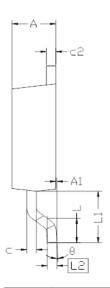
b. Guaranteed by design, not subject to production testing.

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Package Information







CVMDEI	DIMENS:			
SYMBOL	MIN	NDM	MAX	
E	6.40	6.60	6.731	
L	1.40	1.52	1.77	
L1		.743 RI		
L2	0.	.508 BS		
L3	0.89		1.27	
L4	0.64		1.01	
L5				
D	6.00	6.10	6,223	
Н	9.40	10.00	10.40	
b	0.64	0.76	0.88	
b2	0.77	0.84	1.14	
b3	5.21	5.34	5.46	
е	2.286 BSC			
Α	2,20	2.30	2,38	
A1	0		0.127	
_	0.45	0.50	0.60	
c2	0.45	0.50	0,58	
D1	5.30			
E1	4.40			
θ	0°		10°	

Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.